

JST25T-600B 25A TRIAC

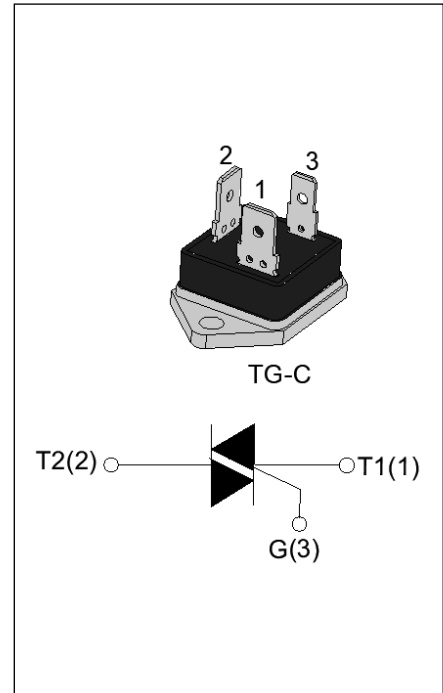
Rev.A.1.0

DESCRIPTION:

The JST25T-600B triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. By using a DBC, JST25T-600B provides a rated insulation voltage of 2500 VRMS, complying with UL standards (File ref: E252906). Package TG-C is RoHS compliant.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	25	A
V_{DRM}/V_{RRM}	600	V
$I_{GT\ I/II/III/IV}$	50/50/50/70	mA


ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T _{stg}	-40-150	℃
Operating junction temperature range		T _j	-40-125	℃
Repetitive peak off-state voltage (T _j =25℃)		V _{DRM}	600	V
Repetitive peak reverse voltage (T _j =25℃)		V _{RRM}	600	V
RMS on-state current (T _c ≤90℃)		I _{T(RMS)}	25	A
Non repetitive surge peak on-state current (full cycle , t _p =20ms , T _j =25℃)		I _{TSM}	250	A
Non repetitive surge peak on-state current (full cycle , t _p =16.6ms , T _j =25℃)			275	
I ² t value for fusing (t _p =10ms , T _j =25℃)		I ² t	340	A ² s
Critical rate of rise of on-state current (I _G =2×I _{GT} , f=100Hz , T _j =125℃)	I - II	di/dt	100	A/μs
	III-IV		50	
Peak gate current (t _p =20μs , T _j =125℃)		I _{GM}	4	A
Average gate power dissipation (T _j =125℃)		P _{G(AV)}	0.5	W
Peak gate power		P _{GM}	10	W

Peak pulse voltage ($T_j=25^{\circ}\text{C}$; non-repetitive, off-state; FIG.7)	V_{pp}	2	kV
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ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12\text{V}$ $R_L=33\Omega$	I - II - III	MAX.	50	mA
		IV		70	
V_{GT}		ALL	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^{\circ}\text{C}$ $R_L=3.3\text{k}\Omega$	ALL	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	I - III - IV	MAX.	80	mA
		II		120	
I_H	$I_T=500\text{mA}$		MAX.	80	mA
dV/dt	$V_D=400\text{V}$ Gate Open $T_j=125^{\circ}\text{C}$		MIN.	1200	V/ μs
$(dV/dt)_c$	$(dI/dt)_c=13.3\text{A/ms}$, $T_j=125^{\circ}\text{C}$		MIN.	12	V/ μs
t_{on}	$I_G=80\text{mA}$ $I_A=250\text{mA}$ $I_R=25\text{mA}$ $T_j=25^{\circ}\text{C}$		TYP.	3	μs
t_{off}				50	

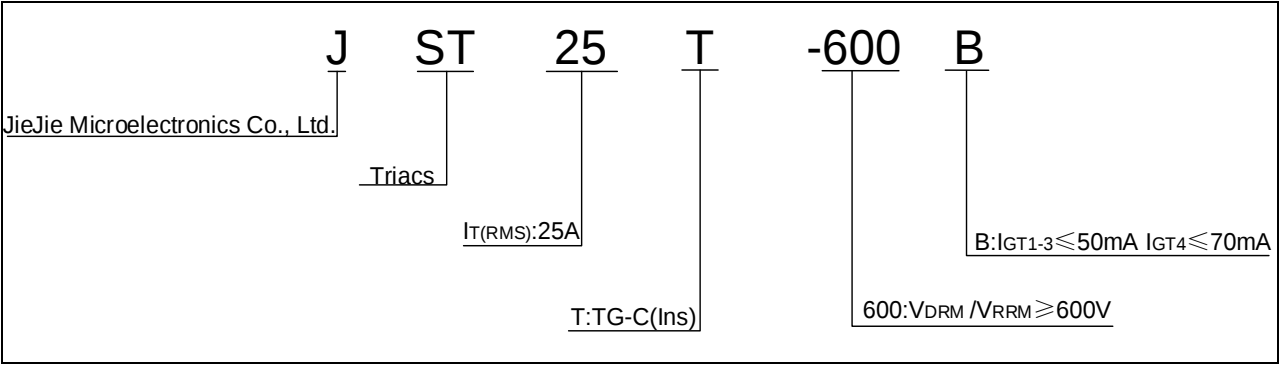
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=35\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.5	V
V_{TO}	Threshold voltage	$T_j=125^{\circ}\text{C}$	0.75	V
R_D	Dynamic resistance	$T_j=125^{\circ}\text{C}$	18	$\text{m}\Omega$
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	5	μA
I_{RRM}		$T_j=125^{\circ}\text{C}$	1.5	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1.0	$^{\circ}\text{C/W}$
$R_{th(j-a)}$	junction to ambient (AC)	45	$^{\circ}\text{C/W}$

ORDERING INFORMATION



MARKING

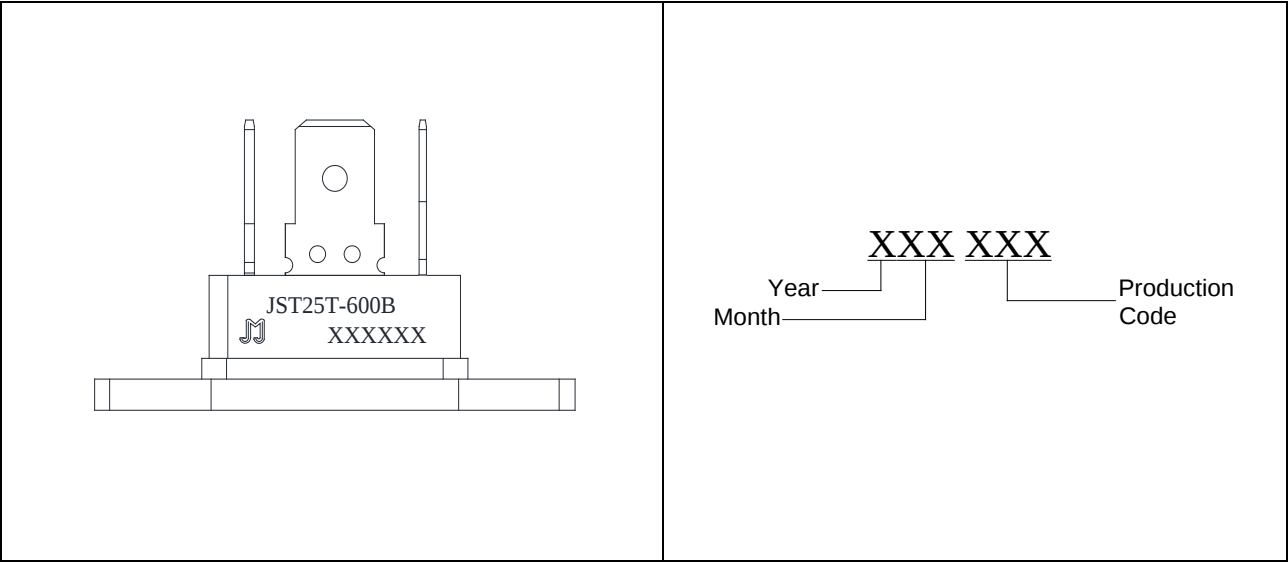


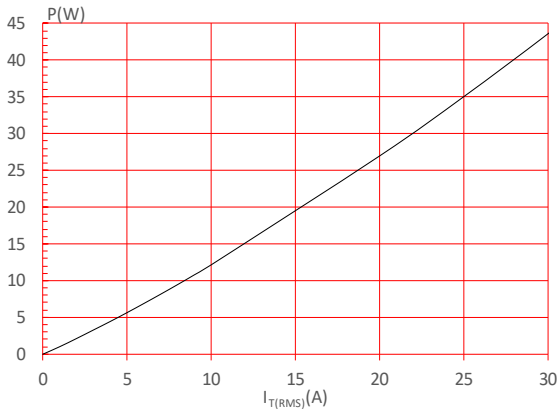
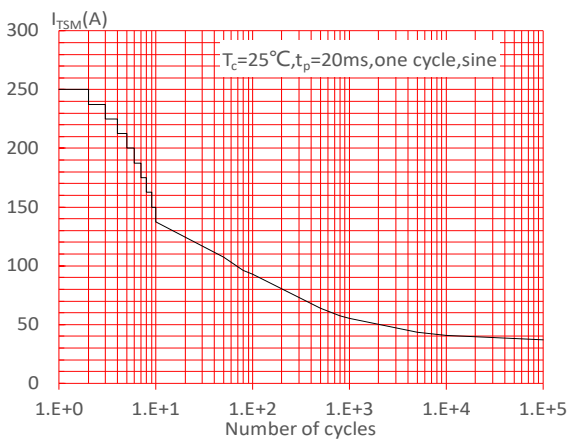
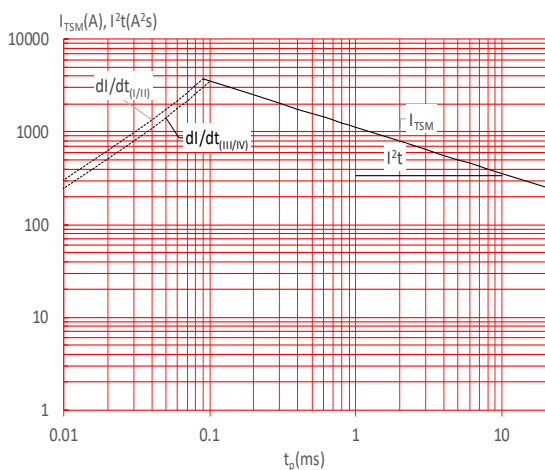
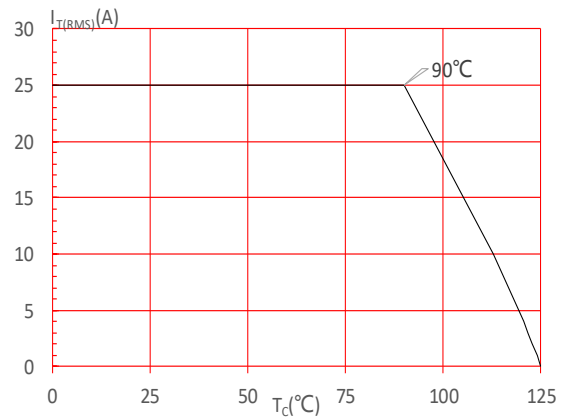
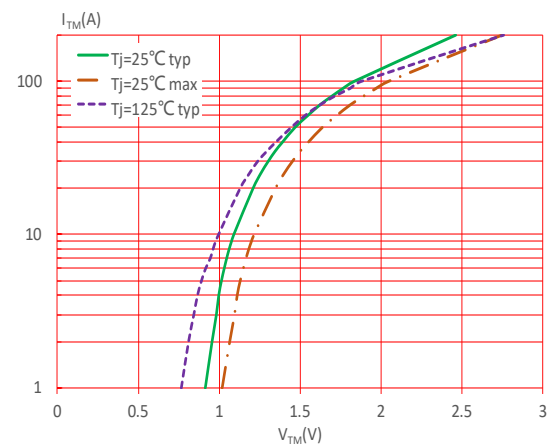
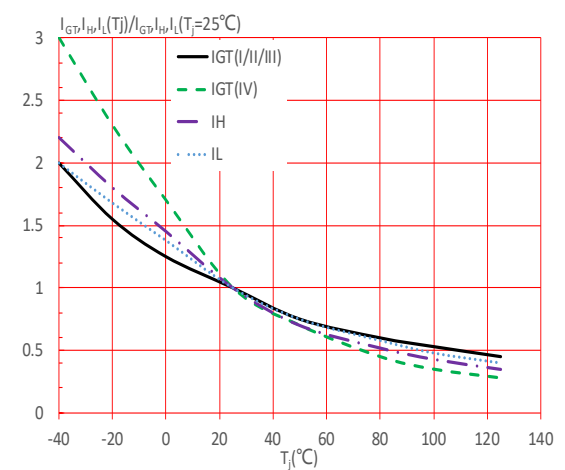
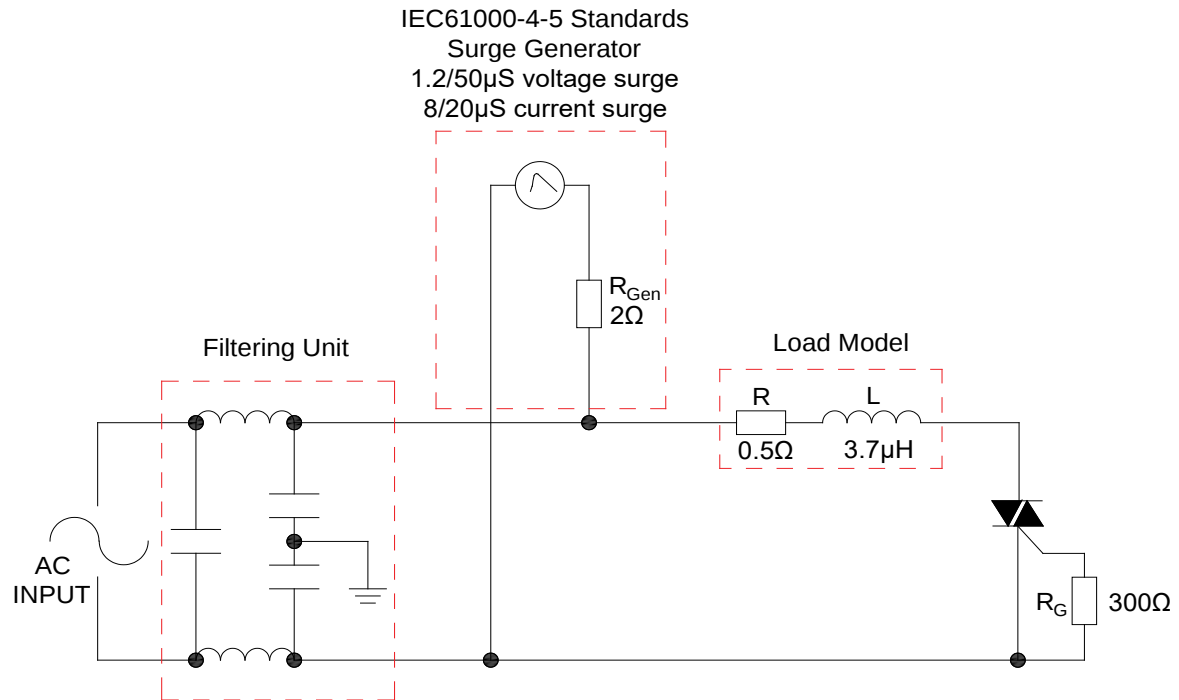
FIG.1: Maximum power dissipation versus RMS on-state current

FIG.3: Surge peak on-state current versus number of cycles

FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t (I - II: $di/dt < 100\text{A}/\mu\text{s}$; III-IV: $di/dt < 50\text{A}/\mu\text{s}$)

FIG.2: RMS on-state current versus case temperature

FIG.4: On-state characteristics

FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



LEAD FORMING AND SOLDERING

Refer to the application note "Assembly Instructions for Thyristors in Through-hole Package" released by JieJie Microelectronics.

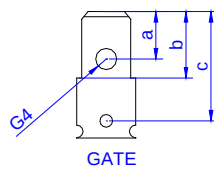
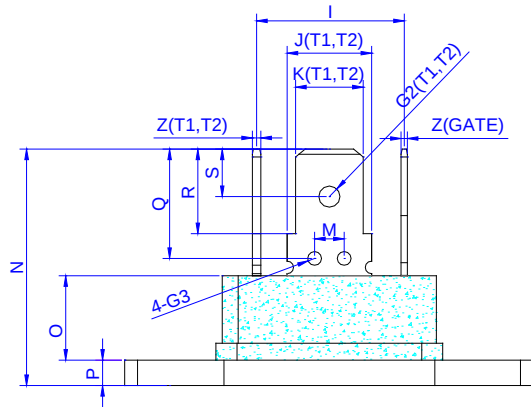
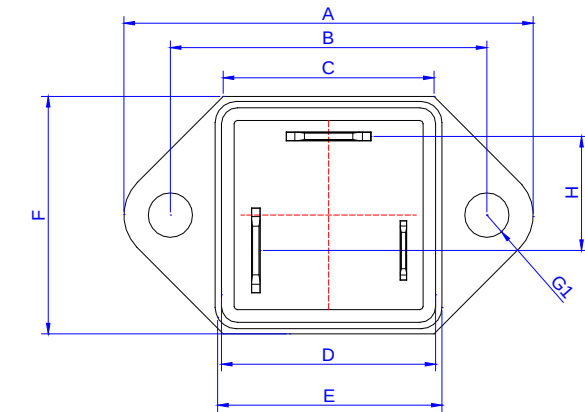
ORDERING INFORMATION

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)		Package	Base qty. (pcs)	Delivery mode
		I - II - III	IV			
JST25T-600B	600	50	70	TG-C(Ins)	10	Tube

Document Revision History

Date	Revision	Changes
Apr.14, 2023	A.1.0	Last updated

PACKAGE MECHANICAL DATA



TG-C

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			39.2			1.543
B	29.8	30.0	30.2	1.173	1.181	1.189
C			20.2			0.795
D			20.5			0.807
E			21.6			0.85
F			23			0.905
G1	Φ4.1	Φ4.2	Φ4.3	Φ0.161	Φ0.165	Φ0.169
H		10.3			0.406	
I		13.9			0.547	
J(T1,T2)		8			0.315	
K(T1,T2)		6.4			0.252	
M	2.7	3.0	3.3	0.106	0.118	0.130
N			22.8			0.898
O		8.2			0.323	
P		2.5			0.098	
Q	9.45	9.75	10.1	0.374	0.383	0.398
R	7.8	7.95	8.1	0.307	0.313	0.319
S	4.3	4.5	4.7	0.169	0.177	0.185
Z(T1,T2)	0.78	0.8	0.85	0.0307	0.0315	0.0335
G2(T1,T2)		Φ2	Φ2.2		Φ0.079	Φ0.087
G3	Φ1.1	Φ1.3	Φ1.5	Φ0.043	Φ0.051	Φ0.059
G4		Φ1.55	Φ1.75		Φ0.061	Φ0.069
a	2.95	3.15	3.35	0.116	0.124	0.132
b	6.2	6.35	6.5	0.244	0.25	0.256
c	9.35	9.75	10	0.368	0.384	0.393
Z(GATE)	0.58	0.6	0.65	0.0228	0.0236	0.0256
J(GATE)		5.6			0.221	
K(GATE)		4.65			0.183	

DELIVERY MODE

PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON (PCS)
TG-C	TUBE	10	100	500

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